

Silicon NPN transistor in a TO-92 Plastic Package.

/ Absolute Maximum Ratings(Ta=25)

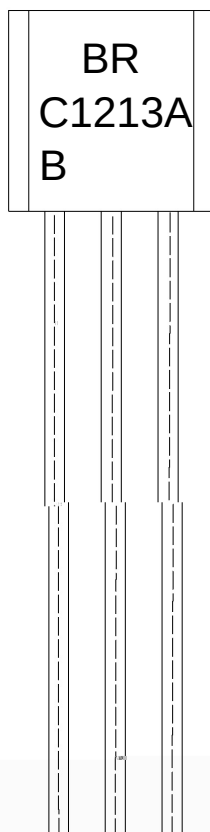
Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	2SC1213	35	V
		2SC1213A	50	
Collector to Emitter Voltage	V_{CEO}	2SC1213	35	V
		2SC1213A	50	
Emitter to Base Voltage	V_{EBO}		4.0	V
Collector Current - Continuous	I_C		500	mA
Collector Power Dissipation	P_C		400	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol		Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	2SC1213	$I_C=10\mu A$ $I_C=1.0mA$	35			V
		2SC1213A		50			
Collector to Emitter Breakdown Voltage	V_{CEO}	2SC1213	$I_C=1.0mA$ $I_B=0$	35			V
		2SC1213A		50			
Emitter to Base Breakdown Voltage	V_{EBO}		$I_E=10\mu A$ $I_C=0$	4.0			V
Collector Cut-Off Current	I_{CBO}		$V_{CB}=20V$ $I_E=0$			0.5	μA
DC Current Gain	$h_{FE(1)}$		$V_{CE}=3.0V$ $I_C=10mA$	60		320	
	$h_{FE(2)}$		$V_{CE}=3.0V$ $I_C=500mA$	10			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$		$I_C=150mA$ $I_B=15mA$		0.2	0.6	V
Base to Emitter Voltage	V_{BE}		$V_{CE}=3.0V$ $I_C=10mA$		0.64		V

/ Package Dimensions

/ Marking Instructions



Note:

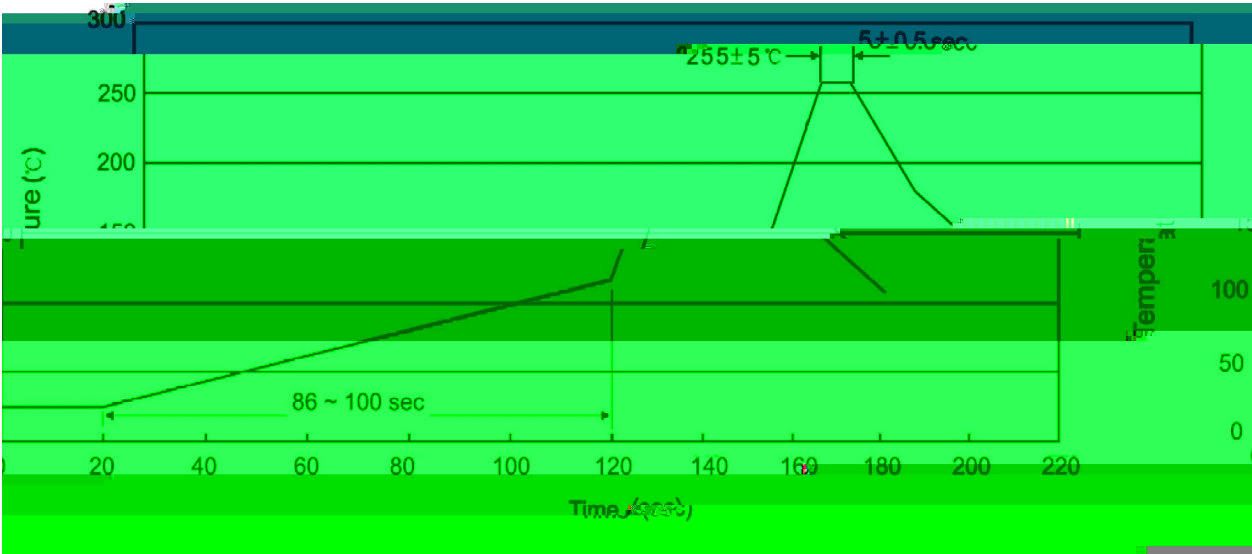
BR: Company Code.

C1213A: Product Type.

B: h_{FE} Classifications Symbol

***: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 , 大箱

/ Notices